

## PATENT ABSTRACTS OF JAPAN

(11)Publication number : 08-008432

(43)Date of publication of application : 12.01.1996

(51)Int.Cl. H01L 29/786

(21)Application number : 06-141812

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(22)Date of filing : 23.06.1994

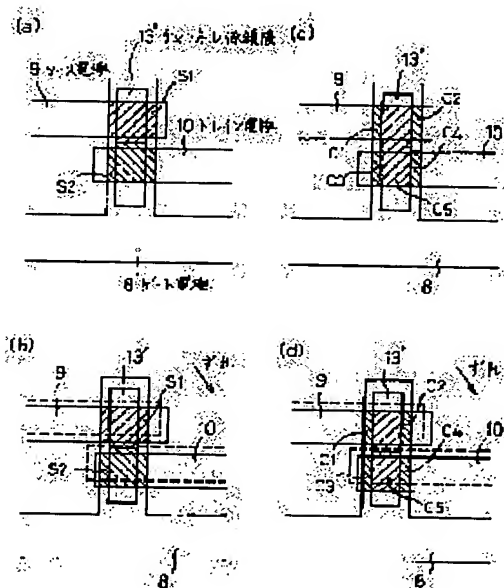
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## (54) THIN FILM TRANSISTOR

## (57)Abstract:

**PURPOSE:** To provide a thin film transistor which can improve display quality of a liquid crystal panel, by eliminating irregularity of parasitic capacitance of a thin film transistor.

**CONSTITUTION:** The channel protecting film 13' of a thin film transistor is formed only on a gate electrode 8. A source electrode 9 and a drain electrode 10 intersect only the two facing sides of a region formed by the channel protecting film 13', and do not overlap with the other sides. The source electrodes 9 and the drain electrode 10 crosswise intersect the gate electrode 8. By this constitution, the value of a parasitic capacitance generated in the part where the thin film transistor is formed can be made constant.



## LEGAL STATUS

[Date of request for examination] 16.01.1998

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number] 3030751

[Date of registration] 10.02.2000

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

▶ [Date of extinction of right]

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